

## SEARCH REQUEST FORM

## Scientific and Technical Information Center

Requester's Full Name: JOHN CHU Examiner #: 68314 Date: 5-2-06  
 Art Unit: 1752 Phone Number 302-1329 Serial Number: 10/523,491  
 Mail Box and Bldg/Room Location: 9051 Results Format Preferred (circle): PAPER DISK E-MAIL

If more than one search is submitted, please prioritize searches in order of need.

\*\*\*\*\*

Please provide a detailed statement of the search topic, and describe as specifically as possible the subject matter to be searched. Include the elected species or structures, keywords, synonyms, acronyms, and registry numbers, and combine with the concept or utility of the invention. Define any terms that may have a special meaning. Give examples or relevant citations, authors, etc, if known. Please attach a copy of the cover sheet, pertinent claims, and abstract.

Title of Invention: \_\_\_\_\_

Inventors (please provide full names): \_\_\_\_\_

Earliest Priority Filing Date: \_\_\_\_\_

\*For Sequence Searches Only\* Please include all pertinent information (parent, child, divisional, or issued patent numbers) along with the appropriate serial number.

PLEASE SEE ATTACHED.

STAFF USE ONLY		Type of Search	Vendors and cost where applicable
Searcher: <u>EJ</u>		NA Sequence (#) <u></u>	STN <u>\$ 229.50</u>
Searcher Phone #: <u></u>		AA Sequence (#) <u></u>	Dialog <u></u>
Searcher Location: <u></u>		Structure (#) <u>✓ (2)</u>	Questel/Orbit <u></u>
Date Searcher Picked Up: <u>4/10/06</u>		Bibliographic <u></u>	Dr.Link <u></u>
Date Completed: <u>5-10-06</u>		Litigation <u></u>	Lexis/Nexis <u></u>
Searcher Prep & Review Time: <u>5</u>		Fulltext <u></u>	Sequence Systems <u></u>
Clerical Prep Time: <u></u>		Patent Family <u></u>	WWW/Internet <u></u>
Time: <u>60</u>		Other <u></u>	Other (specify) <u></u>

**Banks, Kendra**

188361

**From:** JOHN CHU [john.chu@uspto.gov]  
**Sent:** Monday, May 01, 2006 4:21 PM  
**To:** STIC-EIC1700  
**Subject:** Database Search Request, Serial Number: 10/523,491

**Requester:**  
JOHN CHU (P/1752)

**Art Unit:**  
GROUP ART UNIT 1752

**Employee Number:**  
68314

**Office Location:**  
REM 09D51

**Phone Number:**  
(571) 272-1329

**Mailbox Number:**

**Case serial number:**  
10/523,491

**Class / Subclass(es):**  
430/270.1

**Earliest Priority Filing Date:**  
8/9/2002

**Format preferred for results:**  
Paper

**Search Topic Information:**  
Please search the polymer wherein the invention is found in formula (I) and its used in a photoresist composition.

Thank you!

John

**Special Instructions and Other Comments:**

**SCIENTIFIC REFERENCE BR**  
Sci & Tech Inf & Ctr

**MAY 12 REC**

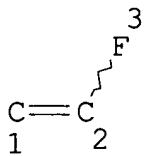
**Pat. & T.M. Office**

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FILE 'REGISTRY' ENTERED AT 13:01:04 ON 10 MAY 2006  
USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.  
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FILE 'LREGISTRY' ENTERED AT 12:57:20 ON 10 MAY 2006  
L1 STR  
L2 STR  
  
FILE 'REGISTRY' ENTERED AT 12:59:12 ON 10 MAY 2006  
L3 SCR 2043  
L4 1 S L1 AND L2 AND L3  
L5 24 S L1 AND L2 AND L3 FUL  
SAV L5 CHU491/A  
  
FILE 'ZCAPLUS' ENTERED AT 13:00:45 ON 10 MAY 2006  
L6 11 S L5  
  
FILE 'CAOLD' ENTERED AT 13:00:50 ON 10 MAY 2006  
L7 0 S L5  
  
FILE 'REGISTRY' ENTERED AT 13:01:04 ON 10 MAY 2006

=> d 15 que stat  
L1 STR

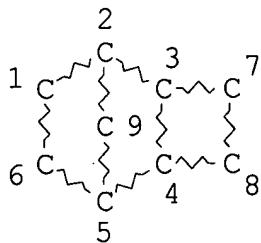


NODE ATTRIBUTES:  
DEFAULT MLEVEL IS ATOM  
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:  
RING(S) ARE ISOLATED OR EMBEDDED  
NUMBER OF NODES IS 3

STEREO ATTRIBUTES: NONE

L2 STR



## NODE ATTRIBUTES:

DEFAULT MLEVEL IS ATOM  
 DEFAULT ECLEVEL IS LIMITED

## GRAPH ATTRIBUTES:

RING(S) ARE ISOLATED OR EMBEDDED  
 NUMBER OF NODES IS 9

## STEREO ATTRIBUTES: NONE

L3 SCR 2043  
 L5 24 SEA FILE=REGISTRY SSS FUL L1 AND L2 AND L3

100.0% PROCESSED 2132 ITERATIONS  
 SEARCH TIME: 00.00.01

24 ANSWERS

=> file zcaplus  
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 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.  
 PLEASE SEE "HELP USAGETERMS" FOR DETAILS.  
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=> d 16 1-11 cbib abs hitstr hitrn

L6 ANSWER 1 OF 11 ZCAPLUS COPYRIGHT 2006 ACS on STN  
 2006:71556 Document No. 144:321347 Bis(fluoroalcohol) Monomers and  
 Polymers: Improved Transparency Fluoropolymer Photoresists for  
 Semiconductor Photolithography at 157 nm. Feiring, Andrew E.;  
 Crawford, Michael K.; Farnham, William B.; French, Roger H.; Leffew,  
 Kenneth W.; Petrov, Viacheslav A.; Schadt, Frank L., III; Tran,  
 Hoang V.; Zumsteg, Fredrick C. (DuPont Central Research Development,  
 Wilmington, DE, 19880-0328, USA). Macromolecules, 39(4), 1443-1448  
 (English) 2006. CODEN: MAMOBX. ISSN: 0024-9297. Publisher:  
 American Chemical Society.

AB Novel norbornene and [4.2.1.02,5]tricyclononene monomers bearing 2

hexafluoro-2-propanol substituents are polymd. with tetrafluoroethylene in soln., giving amorphous, largely alternating copolymers. The norbornene copolymer shows excellent transparency at 157 nm and a dissoln. rate in aq. Me4NOH that is 100,000 times faster than the corresponding polymer with a single hexafluoro-2-propanol substituent on the norbornene ring. Intermediate dissoln. rates are readily obtained using mixts. of the mono- and disubstituted norbornenes. The tricyclononene copolymer is obtained in higher conversion and mol. wt. but has a higher absorbance at 157 nm and a slower dissoln. rate. Partial protection of the fluoroalc. groups as their methoxymethyl derivs. gives photoresist polymers with absorbance of 1.0 .mu.m-1 or less which can be imaged at 157 nm using a photoacid generator.

IT 879175-97-0DP, reaction product with chloromethyl Me ether (fluoroalc. monomers and polymers: improved transparency fluoropolymer photoresists for semiconductor photolithog. at 157 nm)

RN 879175-97-0 ZCAPLUS

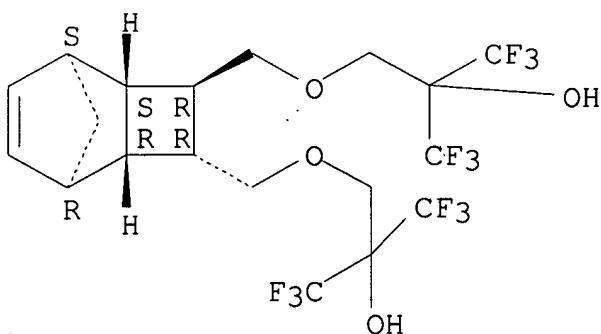
CN 2-Propanol, 2,2'-(1R,2R,3R,4R,5S,6S)-tricyclo[4.2.1.02,5]non-7-ene-3,4-diylbis(methyleneoxymethylene)bis[1,1,1,3,3,3-hexafluoro-, rel-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 879175-82-3

CMF C19 H20 F12 O4

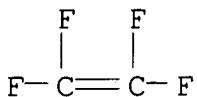
Relative stereochemistry.



CM 2

CRN 116-14-3

CMF C2 F4



IT 879175-97-0P 879176-05-3P

(fluoroalc. monomers and polymers: improved transparency  
 fluoropolymer photoresists for semiconductor photolithog. at 157  
 nm)

RN 879175-97-0 ZCAPLUS

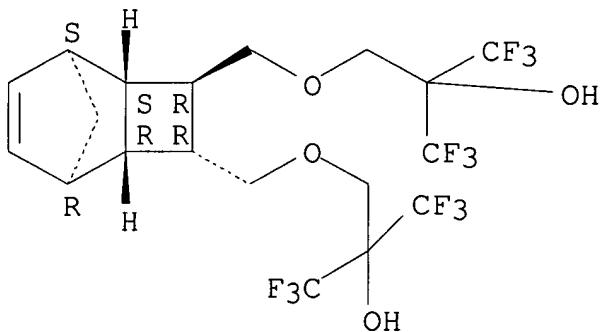
CN 2-Propanol, 2,2'-(1R,2R,3R,4R,5S,6S)-tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3,4-diylbis(methyleneoxymethylene)bis[1,1,1,3,3,3-hexafluoro-, rel-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 879175-82-3

CMF C19 H20 F12 O4

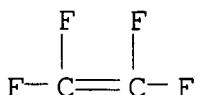
Relative stereochemistry.



CM 2

CRN 116-14-3

CMF C2 F4



RN 879176-05-3 ZCAPLUS

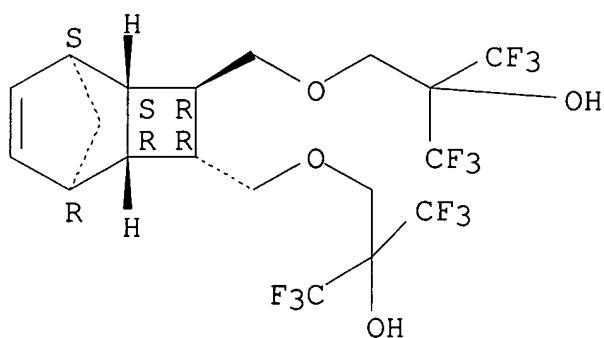
CN 2-Propanol, 2,2'-(1R,2R,3S,4S)-bicyclo[2.2.1]hept-5-ene-2,3-diylbis(oxymethylene)bis[1,1,1,3,3,3-hexafluoro-, rel-, polymer

with tetrafluoroethene and *rel*-2,2'-(*(1R,2R,3R,4R,5S,6S)*-tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3,4-diylbis(methyleneoxymethylene)]bis[1,1,1,3,3,3-hexafluoro-2-propanol] (9CI) (CA INDEX NAME)

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CRN 879175-82-3  
CMF C19 H20 F12 O4

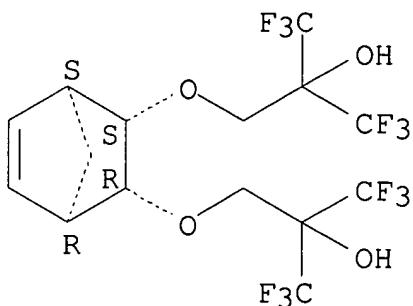
Relative stereochemistry.



CM 2

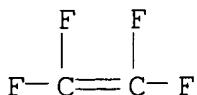
CRN 879175-64-1  
CMF C15 H14 F12 O4

Relative stereochemistry.



CM 3

CRN 116-14-3  
CMF C2 F4

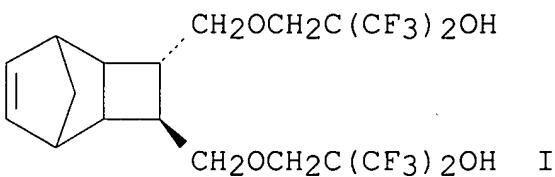


IT **879175-97-0DP**, reaction product with chloromethyl Me ether  
 (fluoroalc. monomers and polymers: improved transparency  
 fluoropolymer photoresists for semiconductor photolithog. at 157  
 nm)

IT **879175-97-0P 879176-05-3P**  
 (fluoroalc. monomers and polymers: improved transparency  
 fluoropolymer photoresists for semiconductor photolithog. at 157  
 nm)

L6 ANSWER 2 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
 2005:1314037 Document No. 144:52079 Photoresists comprising polymers  
 derived from fluoroalcohol-substituted polycyclic monomers.  
 Crawford, Michael Karl; Tran, Hoang Vi; Schadt, Frank L., III;  
 Zumsteg, Frederick Claus, Jr.; Feiring, Andrew Edward; Fryd, Michael  
 (E.I. Dupont De Nemours and Company, USA). PCT Int. Appl. WO  
 2005118656 A2 20051215, 57 pp. DESIGNATED STATES: W: AE, AG, AL,  
 AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU,  
 CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU,  
 ID, IL, IN, IS, JP, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU,  
 LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH,  
 PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT,  
 TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW; RW: AT, BE, BF, BJ, CF,  
 CG, CH, CI, CM, CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IS, IT, LU,  
 MC, ML, MR, NE, NL, PT, SE, SN, TD, TG, TR. (English). CODEN:  
 PIXXD2. APPLICATION: WO 2005-US17325 20050517. PRIORITY: US  
 2004-2004/PV572734 20040520.

GI



AB The invention relates to unsatd. polycyclic compds. contg. two  
 fluoroalc. substituents. The invention also relates to homopolymers  
 and copolymers derived from such unsatd. polycyclic compds. The  
 copolymers are useful for photoimaging compns. and, in particular,  
 photoresist compns. (pos.-working and/or neg.-working) for imaging

in the prodn. of semiconductor devices. The polymers are esp. useful in photoresist compns. having high UV transparency (particularly at short wavelengths, e.g., 157 nm) which are useful as base resins in resists and potentially in many other applications. A typical polymer was manufd. by radical polymn. of 67.5 g fluorodiol I with 30 g tetrafluoroethylene in 1,1,3,3-pentafluorobutane.

IT **871265-69-9DP**, reaction products with chloroalkyl ethers

**871265-71-3P**

(photoresists comprising polymers derived from polycyclic monomers having 2 fluoroalc. groups)

RN 871265-69-9 ZCAPLUS

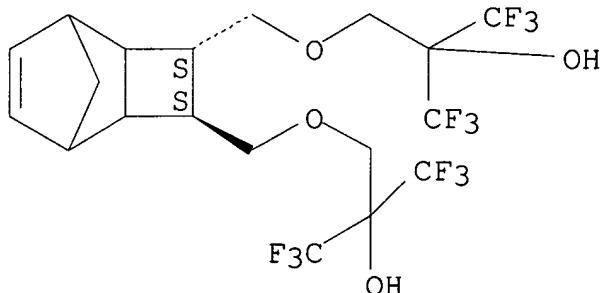
CN 2-Propanol, 2,2'-(3R,4R)-tricyclo[4.2.1.02,5]non-7-ene-3,4-diylbis(methyleneoxymethylene)]bis[1,1,1,3,3,3-hexafluoro-, rel-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 871265-68-8

CMF C19 H20 F12 O4

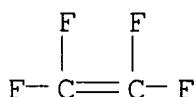
Relative stereochemistry.



CM 2

CRN 116-14-3

CMF C2 F4



RN 871265-71-3 ZCAPLUS

CN Tricyclo[4.2.1.02,5]non-7-ene-3,4-dicarboxylic acid,

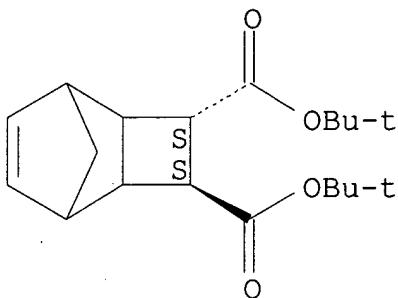
bis(1,1-dimethylethyl) ester, (3S,4S)-rel-, polymer with  
 2,2'-[bicyclo[2.2.1]hept-5-ene-2,3-diylbis(oxymethylene)]bis[1,1,1,3  
 ,3,3-hexafluoro-2-propanol], 2-[(bicyclo[2.2.1]hept-5-en-2-  
 yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol,  
 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate and  
 tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 871265-70-2

CMF C19 H28 O4

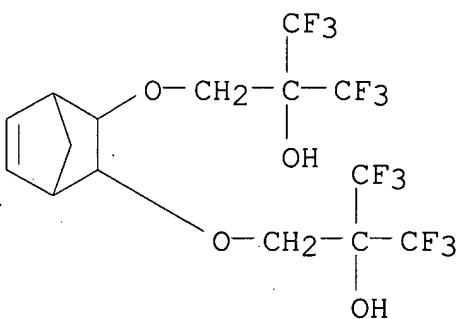
Relative stereochemistry.



CM 2

CRN 871129-88-3

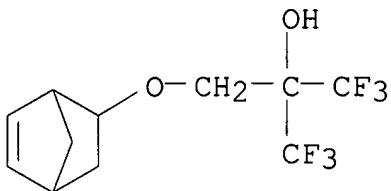
CMF C15 H14 F12 O4



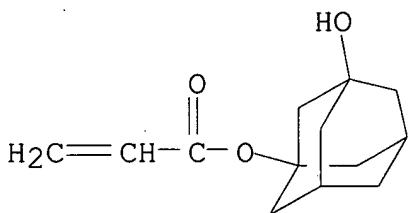
CM 3

CRN 305815-63-8

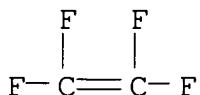
CMF C11 H12 F6 O2



CM 4

CRN 216581-76-9  
CMF C13 H18 O3

CM 5

CRN 116-14-3  
CMF C2 F4IT **871265-69-9P**

(photoresists comprising polymers derived from polycyclic monomers having 2 fluoroalc. groups)

RN 871265-69-9 ZCAPLUS

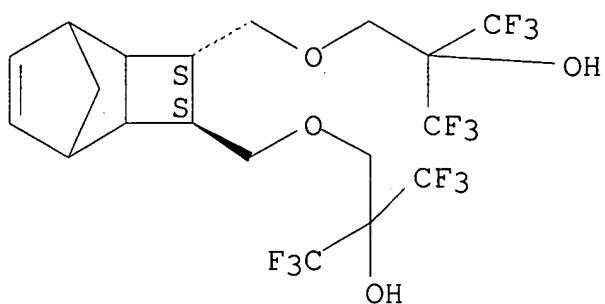
CN 2-Propanol, 2,2'-[ (3R,4R)-tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3,4-diy]bis(methyleneoxymethylene)]bis[1,1,1,3,3,3-hexafluoro-, rel-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 871265-68-8

CMF C19 H20 F12 O4

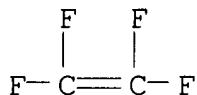
Relative stereochemistry.



CM 2

CRN 116-14-3

CMF C2 F4

IT **871129-97-4P 871265-72-4P**

(photoresists comprising polymers derived from polycyclic monomers having 2 fluoroalc. groups)

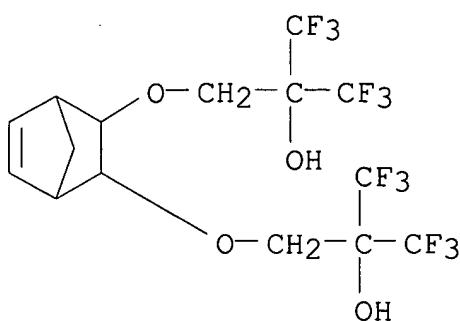
RN 871129-97-4 ZCAPLUS

CN 2-Propenoic acid, 1,1-dimethylethyl ester, polymer with 2,2'-[bicyclo[2.2.1]hept-5-ene-2,3-diylbis(oxymethylene)]bis[1,1,1,3,3,3-hexafluoro-2-propanol], tetrafluoroethylene and 3,3,4,4-tetrafluorotricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene (9CI) (CA INDEX NAME)

CM 1

CRN 871129-88-3

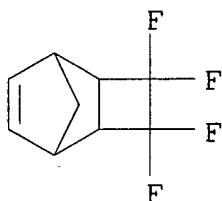
CMF C15 H14 F12 O4



CM 2

CRN 3802-76-4

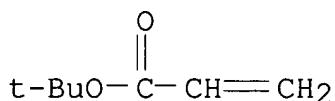
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CM 3

CRN 1663-39-4

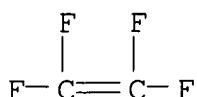
CMF C7 H12 O2



CM 4

CRN 116-14-3

CMF C2 F4



RN 871265-72-4 ZCPLUS

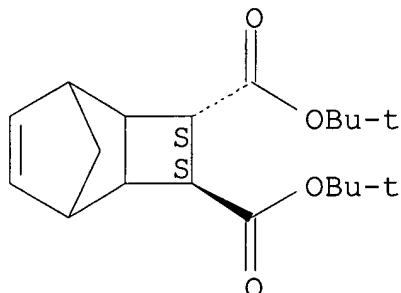
CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3,4-dicarboxylic acid,  
bis(1,1-dimethylethyl) ester, (3S,4S)-rel-, polymer with  
2,2'-[bicyclo[2.2.1]hept-5-ene-2,3-diylbis(oxymethylene)]bis[1,1,1,3  
,3,3-hexafluoro-2-propanol], 6,6,7,7-tetrafluoro-1,4,4a,5,6,7,8,8a-  
octahydro-1,4-methanonaphthalene and tetrafluoroethene (9CI) (CA  
INDEX NAME)

CM 1

CRN 871265-70-2

CMF C19 H28 O4

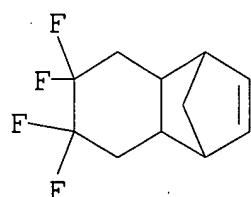
Relative stereochemistry.



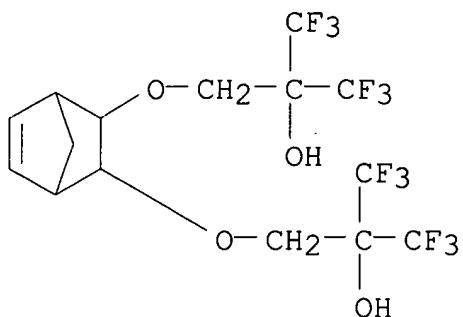
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CRN 871129-98-5

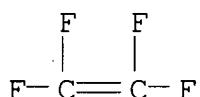
CMF C11 H12 F4



CM 3

CRN 871129-88-3  
CMF C15 H14 F12 O4

CM 4

CRN 116-14-3  
CMF C2 F4IT **871265-69-9P**, reaction products with chloroalkyl ethers  
**871265-71-3P**

(photoresists comprising polymers derived from polycyclic monomers having 2 fluoroalc. groups)

IT **871265-69-9P**

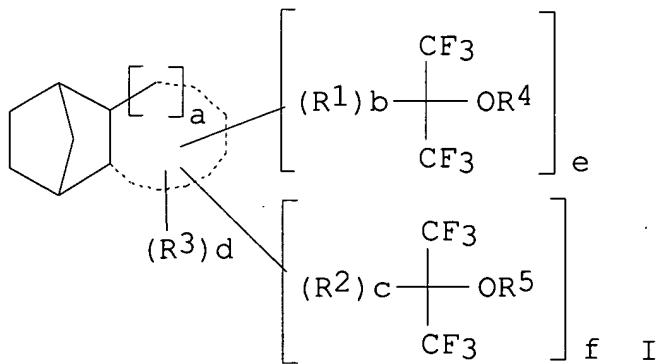
(photoresists comprising polymers derived from polycyclic monomers having 2 fluoroalc. groups)

IT **871129-97-4P 871265-72-4P**

(photoresists comprising polymers derived from polycyclic monomers having 2 fluoroalc. groups)

L6 ANSWER 3 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
 2004:271596 Document No. 140:261423 Trifluoromethyl-containing alicyclic monomers, their polymers, and resist materials containing the polymers. Miyazawa, Satoru; Komoritani, Haruhiko; Maeda, Kazuhiko (Central Glass Co., Ltd., Japan). Jpn. Kokai Tokkyo Koho JP 2004099689 A2 20040402, 28 pp. (Japanese). CODEN: JKXXAF.  
 APPLICATION: JP 2002-261323 20020906.

GI



AB The monomers I [R1, R2 = (fluoro)alkyl which may contain cyclic structure; R3 = H, Cl, F, (fluoro)alkyl which may contain cyclic structure and have OH; R4, R5 = H, group having C1-25 linear, branched, cyclic, or arom. hydrocarbyl which may contain F, O, or CO; a = 1-8; b, c = 0, 1; d, e, f .gtoreq. 0; e + f .gtoreq. 1; d + e + f = 2a] and their homo or copolymers are claimed. Also claimed are resist materials contg. the polymers. The polymers have high transparency to broad wavelength from vacuum UV to optical communication, good adhesion to a substrate, and high etching resistance.

IT **671226-15-6P**

(trifluoromethyl-contg. alicyclic monomers, their polymers, and resist materials contg. the polymers with high transparency to vacuum-UV)

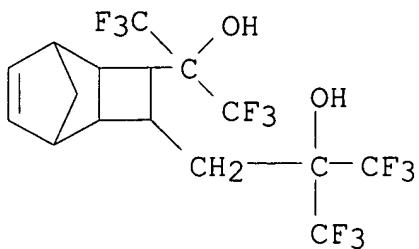
RN 671226-15-6 ZCAPLUS

CN Tricyclo[4.2.1.02,5]non-7-ene-3-ethanol, 4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]-.alpha.,.alpha.-bis(trifluoromethyl)-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

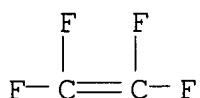
CM 1

CRN 671226-07-6

CMF C16 H14 F12 O2



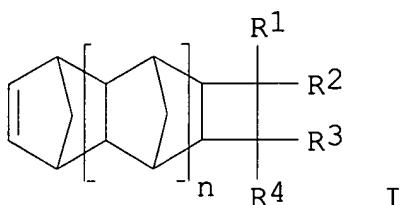
CM 2

CRN 116-14-3  
CMF C2 F4IT **671226-15-6P**

(trifluoromethyl-contg. alicyclic monomers, their polymers, and resist materials contg. the polymers with high transparency to vacuum-UV)

L6 ANSWER 4 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
 2004:220374 Document No. 140:271718 Fluoropolymers for photoresists  
 for 157 nm microlithography. Feiring, Andrew E.; Schadt, Frank L.,  
 III; Petrov, Viacheslav Alexandrovich; Smart, Bruce Edmund; Farnham,  
 William Brown (E. I. Du Pont De Nemours and Company, USA). PCT Int.  
 Appl. WO 2004022612 A1 20040318, 26 pp. DESIGNATED STATES: W: AE,  
 AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR,  
 CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU,  
 ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV,  
 MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO,  
 RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US,  
 UZ, VC, VN, YU, ZA, ZM, ZW; RW: AT, BE, BF, BJ, CF, CG, CH, CI, CM,  
 CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IT, LU, MC, ML, MR, NE, NL,  
 PT, SE, SN, TD, TG, TR. (English). CODEN: PIXXD2. APPLICATION: WO  
 2003-US25023 20030808. PRIORITY: US 2002-2002/PV402225 20020809.

GI



AB The invention provides a polymer having (a) at least one repeat unit derived from an ethylenically unsatd. compd. having at least one fluorine atom covalently attached to an ethylenically unsatd. carbon atom; and (b) at least one repeat unit derived from an ethylenically unsatd. cyclic compd. of structure I; wherein n is 0, 1, or 2; and R1 to R4 are independently H; C1-10 alkyl or alkoxy, optionally substituted by halogen or ether oxygens; or C6-20 aryl. These polymers can be used in making photoresist compns. and coated substrates.

IT **671224-39-8P**

(fluoropolymers for photoresists for 157 nm microlithog.)

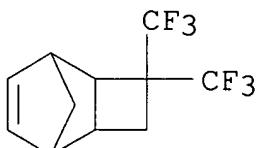
RN 671224-39-8 ZCAPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene, 3,3-bis(trifluoromethyl)-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 671224-38-7

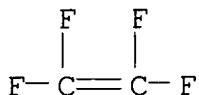
CMF C11 H10 F6



CM 2

CRN 116-14-3

CMF C2 F4

IT **671224-39-8P**

(fluoropolymers for photoresists for 157 nm microlithog.)

L6 ANSWER 5 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
 2004:143196 Document No. 140:181995 Fluorinated polymers having polycyclic groups with fused 4-membered carbocyclic rings, useful as photoresists, and processes for microlithography. Feiring, Andrew E.; Schadt, Frank L., III; Petrov, Viacheslav Alexandrovich; Smart, Bruce Edmund; Farnham, William Brown (E. I. Du Pont De Nemours and Company, USA). PCT Int. Appl. WO 2004014964 A2 20040219, 43 pp.  
 DESIGNATED STATES: W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW; RW: AT, BE, BF, BJ, CF, CG, CH, CI, CM, CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IT, LU, MC, ML, MR, NE, NL, PT, SE, SN, TD, TG, TR. (English).  
 CODEN: PIXXD2. APPLICATION: WO 2003-US25022 20030808. PRIORITY: US 2002-2002/PV40235U 20020809; US 2003-2003/PV440504 20030116.

AB This invention provides novel fluorine contg. polymers which comprise at least one fluorinated olefin, at least one polycyclic ethylenically unsatd. monomer with a fused 4-membered carbocyclic ring and, optionally, other components. The polymers are useful for photoimaging compns. and, in particular, photoresist compns. (pos.-working and/or neg.-working) for imaging in the prodn. of semiconductor devices. The polymers are esp. useful in photoresist compns. having high UV transparency (particularly at short wavelengths, e.g., 157 nm) which are useful as base resins in resists and potentially in many other applications.

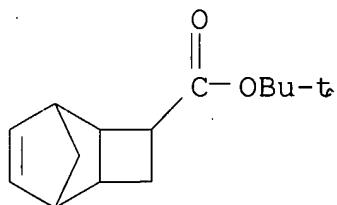
IT **658074-15-8P 658074-16-9P 658074-17-0P****658074-25-0P 658074-26-1P 658074-27-2P****658074-28-3P**

(fluorinated polymers having polycyclic groups with fused 4-membered carbocyclic rings, useful as photoresists, and processes for microlithog.)

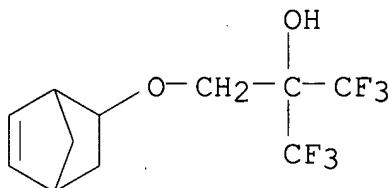
RN 658074-15-8 ZCPLUS

CN Tricyclo[4.2.1.02,5]non-7-ene-3-carboxylic acid, 1,1-dimethylethyl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3-hexafluoro-2-propanol and tetrafluoroethene (9CI) (CA INDEX NAME)

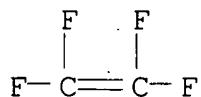
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CRN 473424-70-3  
CMF C14 H20 O2

CM 2

CRN 305815-63-8  
CMF C11 H12 F6 O2

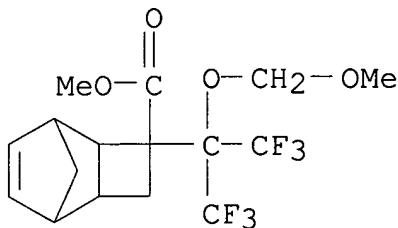
CM 3

CRN 116-14-3  
CMF C2 F4

RN 658074-16-9 ZCPLUS  
 CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3-carboxylic acid,  
 3-[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]-,  
 methyl ester, polymer with tetrafluoroethylene (9CI) (CA INDEX NAME)

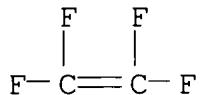
CM 1

CRN 658074-12-5  
 CMF C16 H18 F6 O4



CM 2

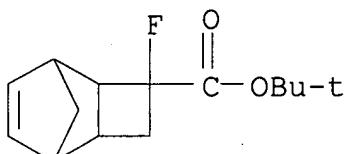
CRN 116-14-3  
 CMF C2 F4



RN 658074-17-0 ZCPLUS  
 CN Tricyclo[4.2.1.02,5]non-7-ene-3-carboxylic acid, 3-fluoro-,  
 1,1-dimethylethyl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-  
 yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol and  
 tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

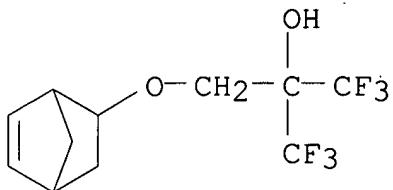
CRN 658074-13-6  
 CMF C14 H19 F O2



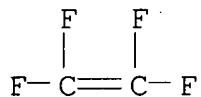
CM 2

CRN 305815-63-8

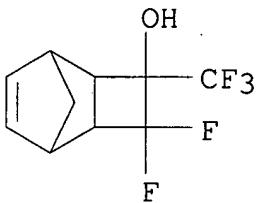
CMF C11 H12 F6 O2



CM 3

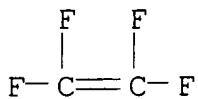
CRN 116-14-3  
CMF C2 F4RN 658074-25-0 ZCAPLUS  
CN Tricyclo[4.2.1.02,5]non-7-en-3-ol, 4,4-difluoro-3-(trifluoromethyl)-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 658074-18-1  
CMF C10 H9 F5 O

CM 2

CRN 116-14-3  
CMF C2 F4



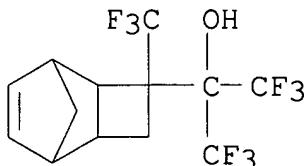
RN 658074-26-1 ZCPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3-methanol, .alpha.,.alpha.,3-tris(trifluoromethyl)-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 658074-20-5

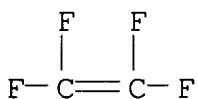
CMF C13 H11 F9 O



CM 2

CRN 116-14-3

CMF C2 F4



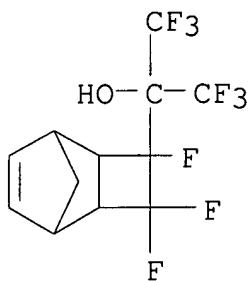
RN 658074-27-2 ZCPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3-methanol, 3,4,4-trifluoro-.alpha.,.alpha.-bis(trifluoromethyl)-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

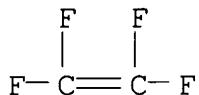
CM 1

CRN 658074-22-7

CMF C12 H9 F9 O

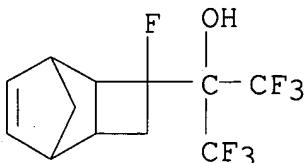


CM 2

CRN 116-14-3  
CMF C2 F4

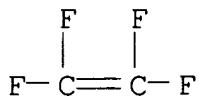
RN 658074-28-3 ZCAPLUS  
 CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3-methanol, 3-fluoro-.alpha.,.alpha.-bis(trifluoromethyl)-, polymer with tetrafluoroethylene (9CI) (CA INDEX NAME)

CM 1

CRN 658074-24-9  
CMF C12 H11 F7 O

CM 2

CRN 116-14-3  
CMF C2 F4



IT 658074-14-7P

(fluorinated polymers having polycyclic groups with fused 4-membered carbocyclic rings, useful as photoresists, and processes for microlithog.)

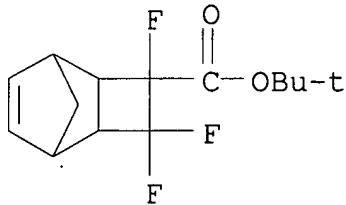
RN 658074-14-7 ZCAPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene-3-carboxylic acid, 3,4,4-trifluoro-, 1,1-dimethylethyl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 658074-10-3

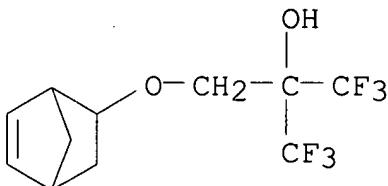
CMF C14 H17 F3 O2



CM 2

CRN 305815-63-8

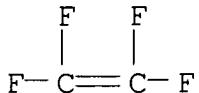
CMF C11 H12 F6 O2



CM 3

CRN 116-14-3

CMF C2 F4



IT **658074-15-8P 658074-16-9P 658074-17-0P**  
**658074-25-0P 658074-26-1P 658074-27-2P**  
**658074-28-3P**

(fluorinated polymers having polycyclic groups with fused 4-membered carbocyclic rings, useful as photoresists, and processes for microlithog.)

IT **658074-14-7P**

(fluorinated polymers having polycyclic groups with fused 4-membered carbocyclic rings, useful as photoresists, and processes for microlithog.)

L6 ANSWER 6 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN

2003:570007 Document No. 140:261269 Progress towards the development of a 157-nm photoresist for carbon dioxide-based lithography.

Zannoni, Luke A.; Simhan, Jay; DeSimone, Joseph M. (Department of Chemistry, Univ. of North Carolina/Chapel Hill, Chapel Hill, NC, 27599, USA). Proceedings of SPIE-The International Society for Optical Engineering, 5039(Pt. 2, Advances in Resist Technology and Processing XX), 1327-1332 (English) 2003. CODEN: PSISDG. ISSN: 0277-786X. Publisher: SPIE-The International Society for Optical Engineering.

AB Photolithog. requires org. solvents and aq. base in the spin-coating, development, and stripping of photoresists. Carbon dioxide, an inexpensive, plentiful, and environmentally sound solvent with tunable solvency, has been proposed as an environmentally friendly alternative to traditional solvents in the electronics industry. Replacing current solvents with CO<sub>2</sub> stems from the inherently low viscosity and surface tension of CO<sub>2</sub>. These properties allow for development of sub 0.1  $\mu$ m images without image collapse, a potential problem in aq. development. Carbon dioxide has been utilized for the synthesis of fluoropolymers. Therefore, given the high solv. of amorphous fluoropolymers in CO<sub>2</sub>, and the necessity of fluoropolymers for the next generation of photolithog. (157 nm), CO<sub>2</sub> may be an environmentally sound solvent for the synthesis, application, development, and stripping of photoresists. To accomplish this goal, several fluorinated monomers (tetrafluoroethylene, chlorotrifluoroethylene, hexafluoropropylene and vinylidene difluoride) have been copolymerd. in dense carbon dioxide with norbornene and norbornene analogs. The resulting polymers have been characterized to det. mol. wt., comonomer

incorporation, Tg, CO<sub>2</sub> solv., and absorbance at 157 nm and 193 nm.  
 Attention: many of the materials described are extremely dangerous,  
 great care should be taken before carrying out any similar expts.

IT **460350-21-4P**

(properties and synthesis of fluoropolymer photoresists in  
 supercrit. CO<sub>2</sub> solvent for 157-nm lithog. using CO<sub>2</sub> as developer  
 and stripper)

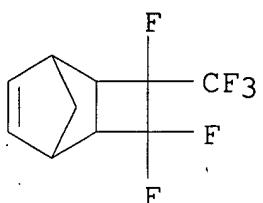
RN 460350-21-4 ZCAPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene, 3,3,4-trifluoro-4-(trifluoromethyl)-,  
 polymer with chlorotrifluoroethylene (9CI) (CA INDEX NAME)

CM 1

CRN 884-95-7

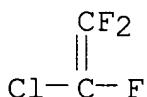
CMF C10 H8 F6



CM 2

CRN 79-38-9

CMF C2 Cl F3



IT **460350-21-4P**

(properties and synthesis of fluoropolymer photoresists in  
 supercrit. CO<sub>2</sub> solvent for 157-nm lithog. using CO<sub>2</sub> as developer  
 and stripper)

L6 ANSWER 7 OF 11 ZCAPLUS COPYRIGHT 2006 ACS on STN

2003:517786 Document No. 139:343402 Design of very transparent  
 fluoropolymer resists for semiconductor manufacture at 157 nm.

Feiring, A. E.; Crawford, M. K.; Farnham, W. B.; Feldman, J.;  
 French, R. H.; Leffew, K. W.; Petrov, V. A.; Schadt, F. L.; Wheland,  
 R. C.; Zumsteg, F. C. (Experimental Station E328/231, Central

Research and Development, E. I. Du Pont de Nemours and Co.,  
 Wilmington, DE, 19880-0328, USA). Journal of Fluorine Chemistry,  
 122(1), 11-16 (English) 2003. CODEN: JFLCAR. ISSN: 0022-1139.  
 Publisher: Elsevier Science B.V..

AB Photolithog. at 157 nm requires development of new photoresists that are highly transparent at this wavelength. Transparent fluoropolymer platforms have been identified which also possess other materials properties required for chem. amplified imaging and aq. development. Polymers of tetrafluoroethylene (TFE), a fluoroalc.-substituted norbornene and an acid-labile acrylate ester show the best combination of properties. A soln., semibatch, free-radical polymn. process was developed allowing synthesis of the terpolymers on a multikilogram scale. Further property enhancements may arise from replacing the norbornene with functionalized tricyclononenes. Formulated resists have been imaged in a 157 nm microstepper.

IT **468728-38-3P**

(design of very transparent fluoropolymer resists for semiconductor manuf. at 157 nm)

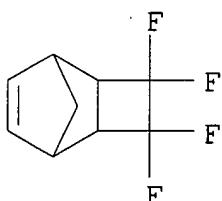
RN 468728-38-3 ZCAPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene, 3,3,4,4-tetrafluoro-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 3802-76-4

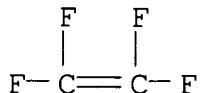
CMF C9 H8 F4



CM 2

CRN 116-14-3

CMF C2 F4



IT **468728-38-3P**

(design of very transparent fluoropolymer resists for semiconductor manuf. at 157 nm)

L6 ANSWER 8 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
2002:778012 Document No. 137:295374 Polycyclic fluorine-containing polymers and photoresists for microlithography. Feiring, Andrew E.; Schadt, Frank L., III (E. I. Du Pont de Nemours & Co., USA). PCT Int. Appl. WO 2002079287 A1 20021010, 36 pp. DESIGNATED STATES: W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM; RW: AT, BE, BF, BJ, CF, CG, CH, CI, CM, CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IT, LU, MC, ML, MR, NE, NL, PT, SE, SN, TD, TG, TR. (English). CODEN: PIXXD2. APPLICATION: WO 2002-US9799 20020327. PRIORITY: US 2001-PV280269 20010330.

AB Polycyclic fluorine-contg. polymers and photoresists and assocd. processes for microlithog. in the extreme, far, and near UV are disclosed. The polycyclic fluorine-contg. polymer is derived from a repeating unit comprising the polycyclic reaction product of norbornadiene and a fluoroolefin. The polymer may also contain a repeat unit derived from one or more addnl. monomers such as a fluoroolefin, specifically tetrafluoroethylene, a fluoroalc., or an acrylate.

IT **468728-38-3P 468728-40-7P 468728-42-9P****468728-44-1P 468728-46-3P**

(polycyclic fluorine-contg. polymers and photoresists for microlithog.)

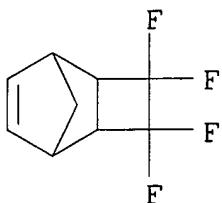
RN 468728-38-3 ZCPLUS

CN Tricyclo[4.2.1.02,5]non-7-ene, 3,3,4,4-tetrafluoro-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

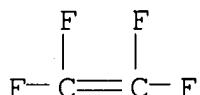
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CRN 3802-76-4

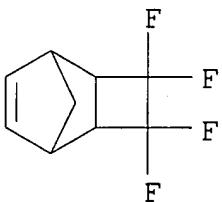
CMF C9 H8 F4



CM 2

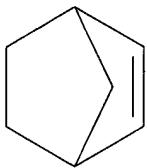
CRN 116-14-3  
CMF C2 F4RN 468728-40-7 ZCPLUS  
CN Tricyclo[4.2.1.02,5]non-7-ene, 3,3,4,4-tetrafluoro-, polymer with  
bicyclo[2.2.1]hept-2-ene and tetrafluoroethene (9CI) (CA INDEX  
NAME)

CM 1

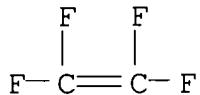
CRN 3802-76-4  
CMF C9 H8 F4

CM 2

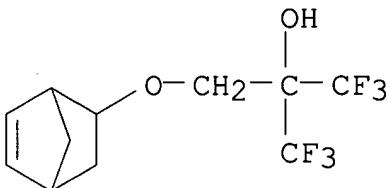
CRN 498-66-8  
CMF C7 H10



CM 3

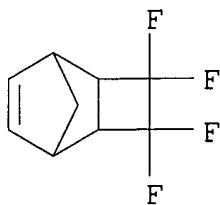
CRN 116-14-3  
CMF C2 F4RN 468728-42-9 ZCPLUS  
CN 2-Propanol, 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-, polymer with tetrafluoroethene and 3,3,4,4-tetrafluorotricyclo[4.2.1.02,5]non-7-ene (9CI) (CA INDEX NAME)

CM 1

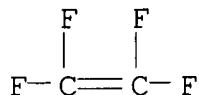
CRN 305815-63-8  
CMF C11 H12 F6 O2

CM 2

CRN 3802-76-4  
CMF C9 H8 F4

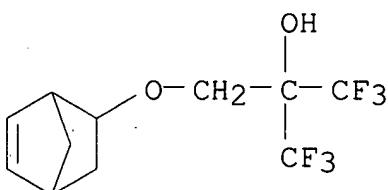


CM 3

CRN 116-14-3  
CMF C2 F4

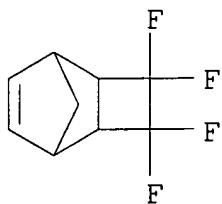
RN 468728-44-1 ZCPLUS  
 CN 2-Propenoic acid, 1,1-dimethylethyl ester, polymer with  
 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-  
 propanol, tetrafluoroethene and 3,3,4,4-  
 tetrafluorotricyclo[4.2.1.02,5]non-7-ene (9CI) (CA INDEX NAME)

CM 1

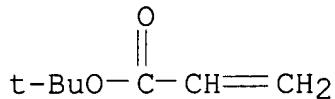
CRN 305815-63-8  
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CM 2

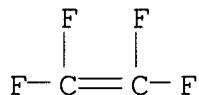
CRN 3802-76-4  
CMF C9 H8 F4



CM 3

CRN 1663-39-4  
CMF C7 H12 O2

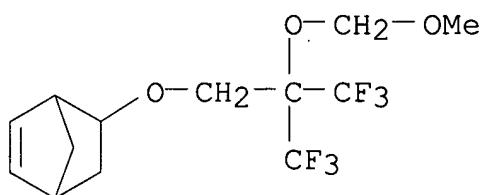
CM 4

CRN 116-14-3  
CMF C2 F4

RN 468728-46-3 ZCAPLUS  
 CN 2-Propanol, 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-, polymer with tetrafluoroethene, 3,3,4,4-tetrafluorotricyclo[4.2.1.02,5]non-7-ene and 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-(trifluoromethyl)propoxy]bicyclo[2.2.1]hept-2-ene (9CI) (CA INDEX NAME)

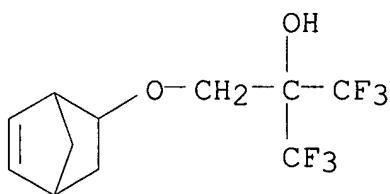
CM 1

CRN 305815-64-9  
CMF C13 H16 F6 O3



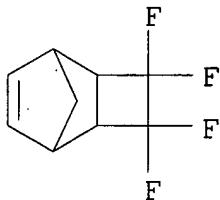
CM 2

CRN 305815-63-8  
 CMF C11 H12 F6 O2



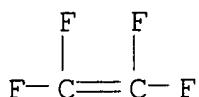
CM 3

CRN 3802-76-4  
 CMF C9 H8 F4



CM 4

CRN 116-14-3  
 CMF C2 F4



IT **468728-38-3P 468728-40-7P 468728-42-9P**  
**468728-44-1P 468728-46-3P**

(polycyclic fluorine-contg. polymers and photoresists for microlithog.)

L6 ANSWER 9 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
 2002:752423 Document No. 137:286448 Photoresists, polymers and processes for microlithography. Feiring, Andrew E.; Schadt, Frank L., III (E. I. Du Pont de Nemours & Co., USA). Eur. Pat. Appl. EP 1246013 A2 20021002, 33 pp. DESIGNATED STATES: R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR. (English). CODEN: EPXXDW. APPLICATION: EP 2002-252281 20020328. PRIORITY: US 2001-PV280268 20010330.

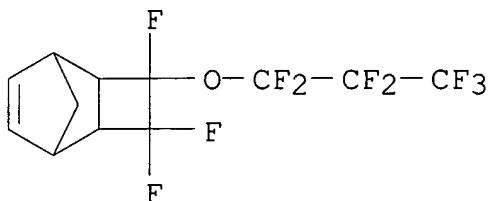
AB Photoresists and assocd. processes for microlithog. in the extreme, far, and near UV are disclosed. The photoresists comprise (a) a fluorine-contg. copolymer comprising a repeat unit derived from at least one ethylenically unsatd. compd. characterized in that at least one ethylenically unsatd. compd. is polycyclic and at least one ethylenically unsatd. compd. contains at least one fluorine atom covalently attached to an ethylenically unsatd. carbon atom; and (b) at least one photoactive component. In other embodiments, the photoresists comprise a fluorine-contg. copolymer comprising a repeat unit derived from at least one polycyclic ethylenically unsatd. compd. having at least one atom or group selected from the group consisting of fluorine atom, perfluoroalkyl group, and perfluoroalkoxy group, characterized in that the at least one atom or group is covalently attached to a carbon atom which is contained within a ring structure and sep'd. from each ethylenically unsatd. carbon atom of the ethylenically unsatd. compd. by at least one covalently attached carbon atom. The photoresists have high transparency in the extreme/far UV as well as the near UV, high plasma etch resistance, and are useful for microlithog. in the extreme, far, and near UV region, particularly at wavelengths < 365 nm. Novel fluorine-contg. copolymers are also disclosed.

IT **262617-20-9P**  
 (photoresists, polymers and processes for microlithog.)

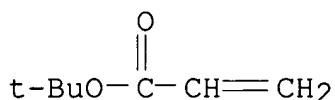
RN 262617-20-9 ZCPLUS

CN 2-Propenoic acid, 1,1-dimethylethyl ester, polymer with tetrafluoroethene and 3,3,4-trifluoro-4-(heptafluoropropoxy)tricyclo[4.2.1.02,5]non-7-ene (9CI) (CA INDEX NAME)

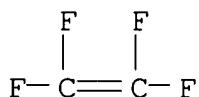
CM 1

CRN 262617-19-6  
CMF C12 H8 F10 O

CM 2

CRN 1663-39-4  
CMF C7 H12 O2

CM 3

CRN 116-14-3  
CMF C2 F4IT **262617-20-9P**

(photoresists, polymers and processes for microlithog.)

L6 ANSWER 10 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
 2002:559899 Document No. 137:255193 Synthesis, characterization and properties of copolymers prepared in dense carbon dioxide towards the development of a 157 nm photoresist. Zannoni, Luke A.; DeSimone, Joseph M. (Department of Chemistry, University of North Carolina at Chapel Hill, Chapel Hill, NC, 27599-3290, USA). PMSE

Preprints, 87, 197-198 (English) 2002. CODEN: PPMRA9. ISSN: 1550-6703. Publisher: American Chemical Society.

AB Synthesis of fluorinated copolymers in CO<sub>2</sub> was studied in order to develop a photoresist which can be spin-coated, developed and stripped with CO<sub>2</sub>. By altering the structure of norbornene co-monomer unit, CO<sub>2</sub> solv. of the polymer was obtained. Caution, many of the materials used are extremely dangerous, great care should be taken before carrying any similar expts.

IT **460350-21-4P 460350-22-5P**  
(synthesis of fluorinated copolymers in dense CO<sub>2</sub> for development of 157 nm photoresist which can be spin-coated, developed and stripped with CO<sub>2</sub>)

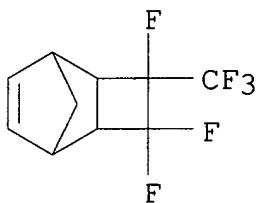
RN 460350-21-4 ZCAPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene, 3,3,4-trifluoro-4-(trifluoromethyl)-, polymer with chlorotrifluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 884-95-7

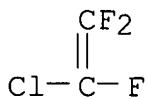
CMF C10 H8 F6



CM 2

CRN 79-38-9

CMF C2 Cl F3

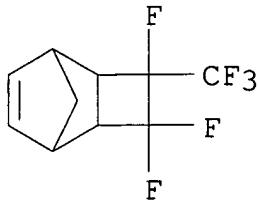


RN 460350-22-5 ZCAPLUS

CN Tricyclo[4.2.1.0<sub>2,5</sub>]non-7-ene, 3,3,4-trifluoro-4-(trifluoromethyl)-, polymer with 1,1-difluoroethene (9CI) (CA INDEX NAME)

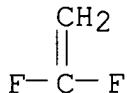
CM 1

CRN 884-95-7  
CMF C10 H8 F6



CM 2

CRN 75-38-7  
CMF C2 H2 F2



IT **460350-21-4P 460350-22-5P**

(synthesis of fluorinated copolymers in dense CO<sub>2</sub> for development of 157 nm photoresist which can be spin-coated, developed and stripped with CO<sub>2</sub>)

L6 ANSWER 11 OF 11 ZCPLUS COPYRIGHT 2006 ACS on STN  
2000:210534 Document No. 132:258158 Photoresist for microlithography. Feiring, Andrew Edward; Feldman, Jerald (E. I. Du Pont de Nemours & Co., USA). PCT Int. Appl. WO 2000017712 A1 20000330, 54 pp.  
DESIGNATED STATES: W: AE, AL, AU, BA, BB, BG, BR, CA, CN, CR, CU, CZ, EE, GD, GE, HR, HU, ID, IL, IN, IS, JP, KP, KR, LC, LK, LR, LT, LV, MG, MK, MN, MX, NO, NZ, PL, RO, SG, SI, SK, SL, TR, TT, UA, US, UZ, VN, YU, ZA, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM; RW: AT, BE, BF, BJ, CF, CG, CH, CI, CM, CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IT, LU, MC, ML, MR, NE, NL, PT, SE, SN, TD, TG. (English). CODEN: PIXXD2. APPLICATION: WO 1999-US21912 19990921. PRIORITY: US 1998-101502 19980923; US 1999-120045 19990212.

AB A photoresist for microlithog. in the extreme, far, and near UV is disclosed. The photoresist comprises (a) a fluorine-contg. copolymer comprising a repeat unit derived from at least one ethylenically unsatd. compd. characterized in that at least one ethylenically unsatd. compd. is polycyclic and at least one ethylenically unsatd. compd. contains at least one fluorine atom covalently attached to an ethylenically unsatd. carbon atom and (b)

at least one photoactive component. In other embodiments, the photoresist comprises a fluorine-contg. copolymer comprising a repeat unit derived from at least one polycyclic ethylenically unsatd. compd. having at least one atom or group selected from the group consisting of fluorine atom, perfluoroalkyl group, and perfluoroalkoxy group, characterized in that the at least one atom or group is covalently attached to a carbon atom which is contained within a ring structure and sep'd. from each ethylenically unsatd. carbon atom of the ethylenically unsatd. compd. by at least one covalently attached carbon atom.

IT **262617-20-9P**

(prepn. and use in prep. UV photoresists for microlithog.)

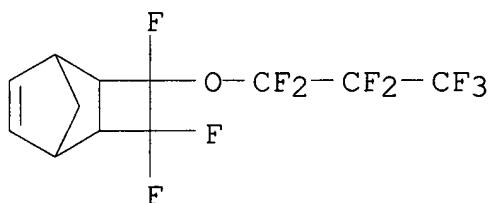
RN 262617-20-9 ZCAPLUS

CN 2-Propenoic acid, 1,1-dimethylethyl ester, polymer with tetrafluoroethene and 3,3,4-trifluoro-4-(heptafluoropropoxy)tricyclo[4.2.1.02,5]non-7-ene (9CI) (CA INDEX NAME)

CM 1

CRN 262617-19-6

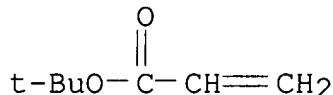
CMF C12 H8 F10 O



CM 2

CRN 1663-39-4

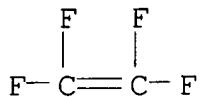
CMF C7 H12 O2



CM 3

CRN 116-14-3

CMF C2 F4



IT **262617-20-9P**

(prepn. and use in prep. UV photoresists for microlithog.)



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Bib Data Sheet

CONFIRMATION NO. 3860

SERIAL NUMBER 10/523,491	FILING OR 371(c) DATE 02/03/2005 RULE	CLASS 430	GROUP ART UNIT 1752	ATTORNEY DOCKET NO. SR0019USPCT
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## \*\* CONTINUING DATA \*\*\*\*\*

This application is a 371 of PCT/US03/25022 08/08/2003  
 which claims benefit of 60/402,350 08/09/2002  
 and claims benefit of 60/440,504 01/16/2003 \*

(\*)Data provided by applicant is not consistent with PTO records.

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

Foreign Priority claimed	<input type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY DE	SHEETS DRAWING	TOTAL CLAIMS 45	INDEPENDENT CLAIMS 4
35 USC 119 (a-d) conditions met	<input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance				
Verified and Acknowledged	Examiner's Signature	Initials			

## ADDRESS

E I du Pont de Nemours & Company  
 Legal Patents  
 Wilmington ,DE 19898

## TITLE

Fluorinated polymers having polycyclic groups with fused 4-membered carbocyclic rings, useful as photoresists, and processes for microlithography

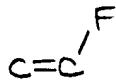
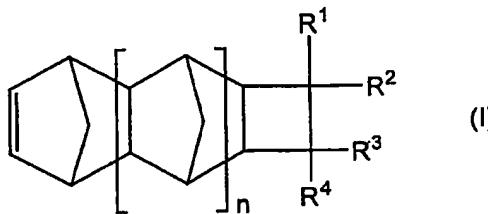
FILING FEE RECEIVED 2350	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:	<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees ( Filing ) <input type="checkbox"/> 1.17 Fees ( Processing Ext. of time ) <input type="checkbox"/> 1.18 Fees ( Issue ) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit
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CLAIMS

What is claimed is:

1. A polymer comprising a repeat unit derived from
  - (a) at least one repeat unit derived from an ethylenically unsaturated compound having at least one fluorine atom covalently attached to an ethylenically unsaturated carbon atom; and
  - (b) at least one repeat unit derived from an ethylenically unsaturated compound having the structure:

10



subset:  
 $\text{CF}_2\text{-OH}$   
 or  
 $\text{C}-\text{OH}$   
 $\text{C}-\text{F}$   
 or  
 $-\text{F}$

wherein n is 0, 1, or 2;

15      R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub> and R<sub>4</sub> are independently H, OR<sup>5</sup>, halogen, alkyl or alkoxy of 1 to 10 carbon atoms, optionally substituted by halogen or ether oxygens, Y, C(R<sub>f</sub>)(R<sub>f'</sub>)OR<sup>5</sup>, R<sup>6</sup>Y or OR<sup>6</sup>Y;

Y is COZ or SO<sub>2</sub>Z;

R<sup>5</sup> is hydrogen or an acid-labile protecting group;

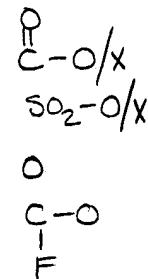
20      R<sub>f</sub> and R<sub>f'</sub> are the same or different fluoroalkyl groups of 1 to 10 carbon atoms or taken together are (CF<sub>2</sub>)<sub>m</sub> where m is 2 to 10;

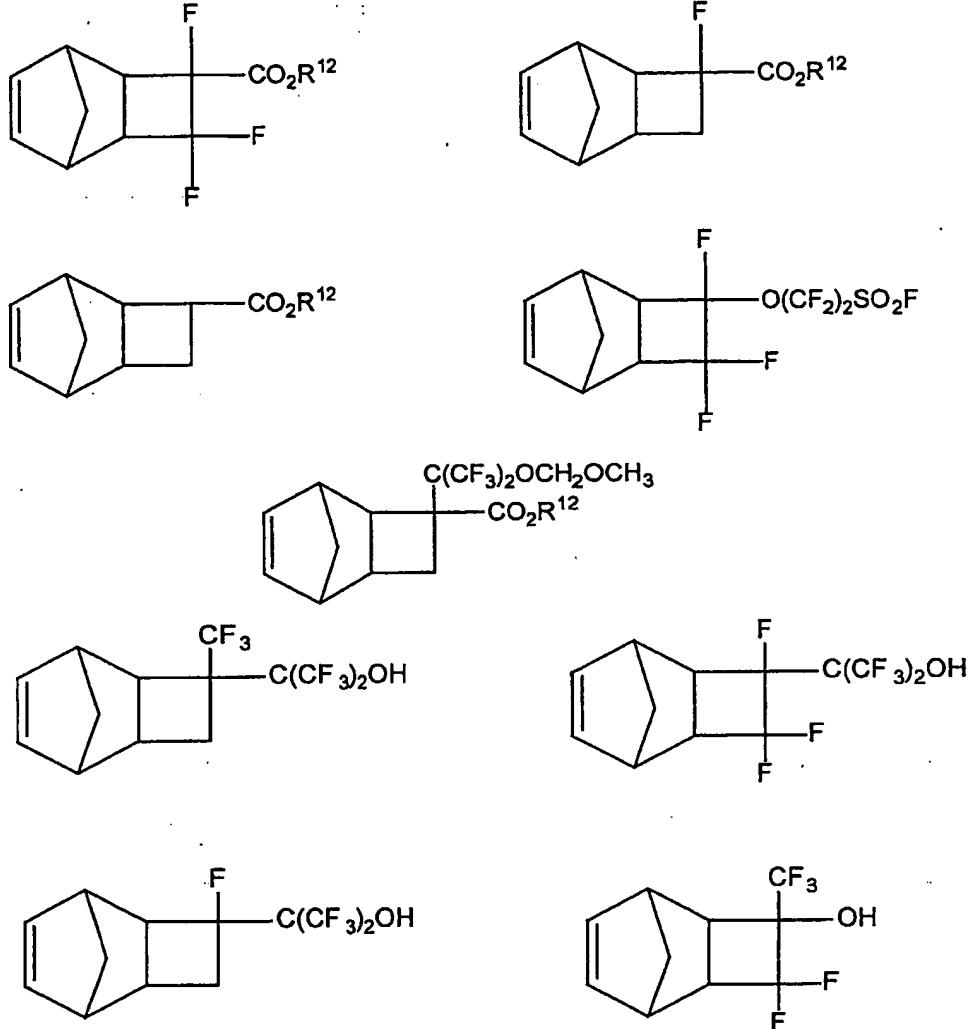
R<sup>6</sup> is an alkylene group of 1 to 20 carbon atoms, optionally substituted by halogen or ether oxygen;

Z is OH, halogen, or OR<sup>7</sup>; and

25      R<sup>7</sup> is an alkyl group of 1 to 20 carbon atoms, with the proviso that at least one of R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub> and R<sub>4</sub> is Y, OR<sup>5</sup>, C(R<sub>f</sub>)(R<sub>f'</sub>)OR<sup>5</sup>, R<sup>6</sup>Y or OR<sup>6</sup>Y, and the proviso that if R<sub>1</sub> (or R<sub>3</sub>) is OH, R<sub>2</sub> (or R<sub>4</sub>) is not OH or halogen.

2. The polymer of Claim 1, wherein the compound having structure (I) is selected from the group consisting of:



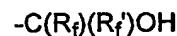


wherein R<sup>12</sup> is an alkyl group of 1 to 20 carbon atoms.

- 5 3. The polymer of Claim 1, wherein the at least one ethylenically unsaturated compound having at least one fluorine atom covalently attached to an ethylenically unsaturated carbon atom is a fluoroolefin which comprises 2 to 20 carbon atoms.
4. The polymer of Claim 3, wherein the fluoroolefin is selected from the group consisting of tetrafluoroethylene; hexafluoropropylene; chlorotrifluoroethylene; vinylidene fluoride; vinyl fluoride; perfluoro-(2,2-dimethyl-1,3-dioxole); perfluoro-(2-methylene-4-methyl-1,3-dioxolane);

$CF_2=CFO(CF_2)_tCF=CF_2$ , wherein t is 1 or 2; and  $R_f''OCF=CF_2$  wherein  $R_f''$  is a saturated fluoroalkyl group of from 1 to 10 carbon atoms.

- 5        5. The polymer of Claim 4, wherein the fluoroolefin is tetrafluoroethylene.
- 5        6. The polymer of Claim 1, further comprising a unit containing a fluoroalcohol group or a protected fluoroalcohol group.
- 10        7. The polymer of Claim 6, wherein the fluoroalcohol group or the protected fluoroalcohol group is derived from at least one ethylenically unsaturated compound containing a fluoroalcohol group having the structure:



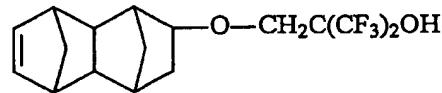
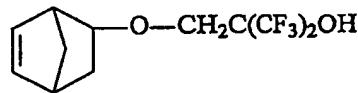
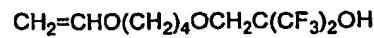
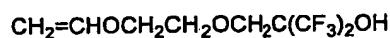
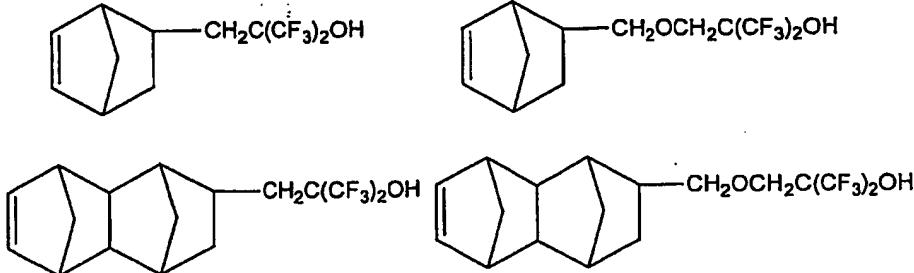
15        wherein  $R_f$  and  $R_f'$  are the same or different fluoroalkyl groups of from 1 to 10 carbon atoms or taken together are  $(CF_2)_m$  wherein m is 2 to 10.

- 15        8. The polymer of Claim 7, wherein  $R_f$  and  $R_f'$  are perfluoroalkyl groups.
- 20        9. The polymer of Claim 1, further comprising a unit containing a fluoroalcohol group having the structure:



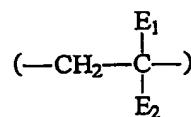
25        wherein  $R_f$  and  $R_f'$  are the same or different fluoroalkyl groups of from 1 to 10 carbon atoms or taken together are  $(CF_2)_m$  wherein m is 2 to 10; and X is an element from Group VA or Group VIA of the Periodic Table of the Elements.

- 25        10. The polymer of Claim 9, wherein X is selected from the group consisting of oxygen, sulfur, nitrogen and phosphorous.
- 30        11. The polymer of Claim 10, wherein X is oxygen.
- 30        12. The polymer of Claim 7, wherein fluoroalcohol group or the protected fluoroalcohol group is derived from a monomer selected from the group consisting of:



5

13. The polymer of Claim 1 further comprising at least one acid-containing or protected acid-containing group of structural unit:



10

wherein  $\text{E}_1$  is H or  $\text{C}_1\text{-C}_{12}$  alkyl;  $\text{E}_2$  is  $\text{CO}_2\text{E}_3$ ,  $\text{SO}_3\text{E}$ , or other acidic group; and  $\text{E}$  and  $\text{E}_3$  are independently selected from the group of H, unsubstituted  $\text{C}_1\text{-C}_{12}$  alkyl, and heteroatom substituted  $\text{C}_1\text{-C}_{12}$  alkyl.

14. The polymer of Claim 13, wherein the heteroatom is selected from the group consisting of oxygen, nitrogen, sulfur, halogen and phosphorus atoms.

15. The polymer of Claim 14, wherein the heteroatom is oxygen, and the heteroatom substituted  $\text{C}_1\text{-C}_{12}$  alkyl further comprises a hydroxyl group.

20 16. The polymer of Claim 13, wherein the acid-containing or protected acid-containing group is derived from a carboxylic acid-containing monomer.

17. The polymer of Claim 13, wherein the acid-containing or protected acid-containing group is derived from a monomer selected from the group consisting of tert-butyl acrylate; 2-methyl-2-adamantyl acrylate; 2-methyl-2-norbornyl acrylate and acrylic acid.

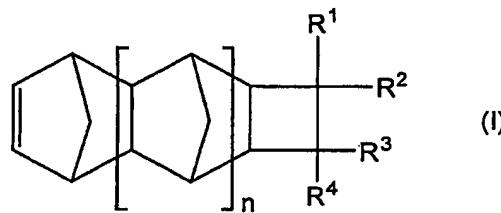
5 18. The polymer of Claim 1, further comprising at least one group derived from a polar monomer.

19. A photoresist composition comprising:

(1) a fluorine-containing polymer, wherein the fluorine-containing polymer comprises:

10 (a) at least one repeat unit derived from an ethylenically unsaturated compound having at least one fluorine atom covalently attached to an ethylenically unsaturated carbon atom; and

15 (b) at least one repeat unit derived from an ethylenically unsaturated compound having the structure:



wherein n is 0, 1, or 2;

20 R<sup>1</sup>, R<sup>2</sup>, R<sup>3</sup> and R<sup>4</sup> are independently H, OR<sup>5</sup>, halogen, alkyl or alkoxy of 1 to 10 carbon atoms, optionally substituted by halogen or ether oxygens, Y, C(R<sub>f</sub>)(R<sub>f'</sub>)OR<sup>5</sup>, R<sup>6</sup>Y or OR<sup>6</sup>Y;

Y is COZ or SO<sub>2</sub>Z;

R<sup>5</sup> is hydrogen or an acid-labile protecting group;

25 R<sub>f</sub> and R<sub>f'</sub> are the same or different fluoroalkyl groups of 1 to 10 carbon atoms or taken together are (CF<sub>2</sub>)<sub>m</sub> where m is 2 to 10;

R<sup>6</sup> is an alkylene group of 1 to 20 carbon atoms, optionally substituted by halogen or ether oxygen;

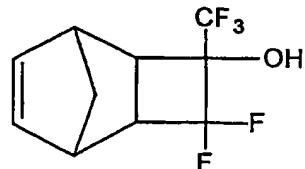
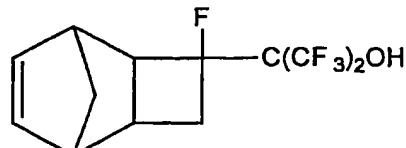
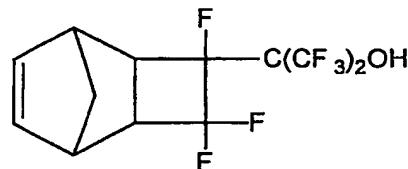
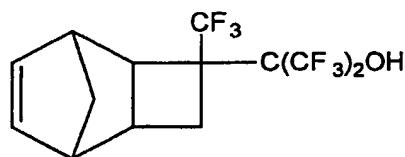
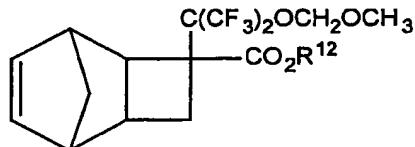
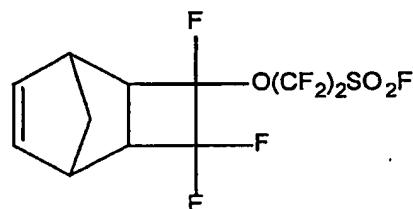
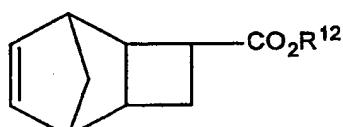
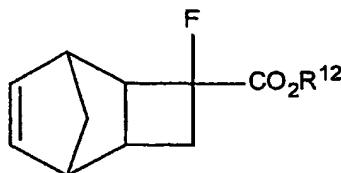
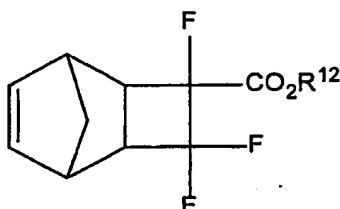
Z is OH, halogen, or OR<sup>7</sup>; and

30 R<sup>7</sup> is an alkyl group of 1 to 20 carbon atoms, with the proviso that at least one of R<sup>1</sup>, R<sup>2</sup>, R<sup>3</sup> and R<sup>4</sup> is OR<sup>5</sup>, Y, C(R<sub>f</sub>)(R<sub>f'</sub>)OR<sup>5</sup>, R<sup>6</sup>Y or OR<sup>6</sup>Y,

and the proviso that if R<sup>1</sup> (or R<sup>3</sup>) is OH, R<sup>2</sup> (or R<sup>4</sup>) is not OH or halogen;  
and

(2) a photoactive component.

20. The photoresist composition of Claim 19, wherein the  
5 monomer having structure (I) in the fluorine-containing polymer is selected  
from the group consisting of:



10

wherein R<sup>12</sup> is an alkyl group of 1 to 20 carbon atoms.

21. The photoresist composition of Claim 19, wherein (a) is a fluoroolefin comprising 2 to 20 carbon atoms.
22. The photoresist composition of Claim 21, wherein the fluoroolefin is selected from the group consisting of tetrafluoroethylene; hexafluoropropylene; chlorotrifluoroethylene; vinylidene fluoride; vinyl fluoride; perfluoro-(2,2-dimethyl-1,3-dioxole); perfluoro-(2-methylene-4-methyl-1,3-dioxolane);  $CF_2=CFO(CF_2)_tCF=CF_2$ , wherein t is 1 or 2; and  $R_f''OCF=CF_2$ , wherein  $R_f''$  is a saturated fluoroalkyl group of from 1 to 10 carbon atoms.
- 10 23. The photoresist composition of Claim 22, wherein the fluoroolefin is tetrafluoroethylene.
24. The photoresist composition of Claim 19, wherein the fluorine-containing polymer further comprises a unit containing a fluoroalcohol group or a protected fluoroalcohol group.
- 15 25. The photoresist composition of Claim 24, wherein the fluoroalcohol group or the protected fluoroalcohol group is derived from at least one ethylenically unsaturated compound containing a fluoroalcohol group having the structure:

20  $-C(R_f)(R_f')OH$

wherein  $R_f$  and  $R_f'$  are the same or different fluoroalkyl groups of from 1 to 10 carbon atoms or taken together are  $(CF_2)_m$  wherein m is 2 to 10.

26. The photoresist composition of Claim 25, wherein  $R_f$  and  $R_f'$  are perfluoroalkyl groups.
27. The photoresist composition of Claim 19, wherein the fluorine-containing polymer further comprises a fluoroalcohol group having the structure:

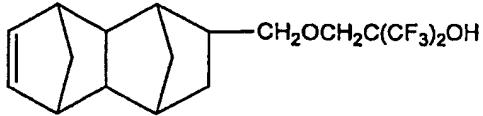
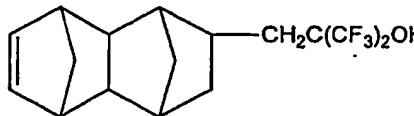
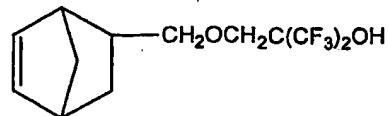
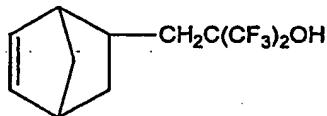
30  $-XCH_2C(R_f)(R_f')OH$

wherein  $R_f$  and  $R_f'$  are the same or different fluoroalkyl groups of from 1 to 10 carbon atoms or taken together are  $(CF_2)_m$  wherein m is 2 to 10; and X is an element from Group VA and VIA of the Periodic Table of the Elements.

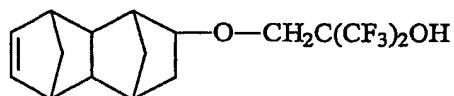
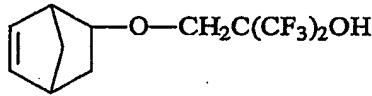
35 28. The photoresist composition of Claim 27, wherein X is selected from the group consisting of oxygen, sulfur, nitrogen and phosphorous.

29. The photoresist composition of Claim 28, wherein X is oxygen.

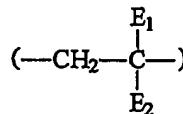
30. The photoresist composition of Claim 25, wherein the monomer containing the fluoroalcohol functional group or the protected fluoroalcohol group is selected from the group consisting of:



5       $\text{CH}_2=\text{CHOCH}_2\text{CH}_2\text{OCH}_2\text{C}(\text{CF}_3)_2\text{OH}$        $\text{CH}_2=\text{CHO}(\text{CH}_2)_4\text{OCH}_2\text{C}(\text{CF}_3)_2\text{OH}$



10      31. The photoresist composition of Claim 19, wherein the fluorine-containing polymer further comprises at least one acid-containing or protected acid-containing group of structural unit:



15

wherein  $\text{E}_1$  is H or  $\text{C}_1\text{-C}_{12}$  alkyl;  $\text{E}_2$  is  $\text{CO}_2\text{E}_3$ ,  $\text{SO}_3\text{E}$ , or other acidic group; and  $\text{E}$  and  $\text{E}_3$  are independently selected from the group of H, unsubstituted  $\text{C}_1\text{-C}_{12}$  alkyl, and heteroatom substituted  $\text{C}_1\text{-C}_{12}$  alkyl.

20      32. The photoresist composition of Claim 31, wherein the heteroatom is selected from the group consisting of oxygen, nitrogen, sulfur, halogen and phosphorus atoms.

33. The photoresist composition of Claim 32, wherein the heteroatom is oxygen, and the heteroatom substituted C<sub>1</sub>-C<sub>12</sub> alkyl further comprises a hydroxyl group.

34. The photoresist composition of Claim 31, wherein the acid-5 containing or protected acid-containing group is a carboxylic acid-containing monomer.

35. The photoresist composition of Claim 34, wherein the acid-containing or protected acid-containing group is selected from the group consisting of tert-butyl acrylate; 2-methyl-2-adamantyl acrylate; 2-methyl-10 2-norbornyl acrylate and acrylic acid.

36. The photoresist composition of Claim 19, wherein the fluorine-containing polymer further comprises at least one group derived from a polar monomer.

37. The photoresist composition of Claim 19, wherein the photoactive component is a photoacid generator.

38. The photoresist composition of Claim 19, further comprising a dissolution inhibitor.

39. The photoresist composition of Claim 19, further comprising a solvent.

40. The photoresist composition of Claim 39, wherein the solvent is selected from the group consisting of an ether ester; a ketone; an ester; a glycol ether; a substituted hydrocarbon; an aromatic hydrocarbon; a fluorinated solvent and super critical CO<sub>2</sub>.

41. The photoresist composition of Claim 19, further comprising at least one additive selected from the group consisting of bases, surfactants, resolution enhancers, adhesion promoters, residue reducers, coating aids, plasticizers, and T<sub>g</sub> (glass transition temperature) modifiers.

42. A coated substrate comprising:

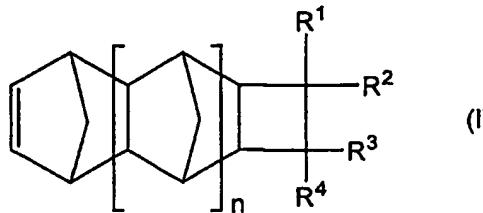
30 (1) a substrate; and

(2) a photoresist composition comprising:

(a) a fluorine-containing polymer comprising a repeat unit derived from:

(i) at least one repeat unit derived from an ethylenically unsaturated compound having at least one fluorine atom covalently attached to an ethylenically unsaturated carbon atom; and

(ii) at least one repeat unit derived from an ethylenically unsaturated compound having the structure:



5

wherein n is 0, 1, or 2;

10 R<sup>1</sup>, R<sup>2</sup>, R<sup>3</sup> and R<sup>4</sup> are independently H, OR<sup>5</sup>, halogen, alkyl or alkoxy of 1 to 10 carbon atoms, optionally substituted by halogen or ether oxygens, Y, C(R<sub>f</sub>)(R<sub>f'</sub>)OR<sup>5</sup>, R<sup>6</sup>Y or OR<sup>6</sup>Y;  
 Y is COZ or SO<sub>2</sub>Z;  
 R<sup>5</sup> is hydrogen or an acid-labile protecting group;  
 R<sub>f</sub> and R<sub>f'</sub> are the same or different fluoroalkyl groups of 1 to 10 carbon atoms or taken together are (CF<sub>2</sub>)<sub>m</sub> where m is 2 to 10;  
 15 R<sup>6</sup> is an alkylene group of 1 to 20 carbon atoms, optionally substituted by halogen or ether oxygen;  
 Z is OH, halogen, or OR<sup>7</sup>; and  
 R<sup>7</sup> is an alkyl group of 1 to 20 carbon atoms, with the proviso that at least one of R<sup>1</sup>, R<sup>2</sup>, R<sup>3</sup> and R<sup>4</sup> is Y, OR<sup>5</sup>, C(R<sub>f</sub>)(R<sub>f'</sub>)OR<sup>5</sup>, R<sup>6</sup>Y or OR<sup>6</sup>Y,  
 20 and the proviso that if R<sup>1</sup> (or R<sup>3</sup>) is OH, R<sup>2</sup> (or R<sup>4</sup>) is not OH or halogen; and

(b) a photoactive component.

43. The coated substrate of Claim 42, wherein the substrate is a microelectronic wafer.

25 44. The coated substrate of Claim 43, wherein the microelectronic wafer comprises a material selected from the group consisting of silicon, silicon oxide, silicon oxynitride, and silicon nitride.

45. A reaction product of quadracyclane and a fluoroalkylbenzoate compound.

30

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

03 FEB 2005

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
19 February 2004 (19.02.2004)

PCT

(10) International Publication Number  
WO 2004/014964 A2

(51) International Patent Classification<sup>7</sup>: C08F 14/18, G03C 1/73

(74) Agent: SINNOTT, Jessica, M.; E. I. DU PONT DE NEMOURS AND COMPANY, Legal Patent Records Center, 4417 Lancaster Pike, Wilmington, DE 19805 (US).

(21) International Application Number: PCT/US2003/025022

(22) International Filing Date: 8 August 2003 (08.08.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
60/402,350 9 August 2002 (09.08.2002) US  
60/440,504 16 January 2003 (16.01.2003) US

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(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EB, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— without international search report and to be republished upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

WO 2004/014964 A2

(54) Title: FLUORINATED POLYMERS HAVING POLYCYCLIC GROUPS WITH FUSED 4-MEMBERED CARBOCYCLIC RINGS, USEFUL AS PHOTORESISTS, AND PROCESSES FOR MICROLITHOGRAPHY

(57) Abstract: This invention provides novel fluorine containing polymers which comprise at least one fluorinated olefin, at least one polycyclic ethylenically unsaturated monomer with a fused 4-membered carbocyclic ring and, optionally, other components. The polymers are useful for photoimaging compositions and, in particular, photoresist compositions (positive-working and/or negative-working) for imaging in the production of semiconductor devices. The polymers are especially useful in photoresist compositions having high UV transparency (particularly at short wavelengths, e.g., 157 nm) which are useful as base resins in resists and potentially in many other applications.